

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2088	(315/169.3).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/01 17:09
S2	1249	(integrated near circuit) and (different near voltage) and CMOS and (PMOS or p\$1type near metal\$1 oxide near semiconductor) and (NMOS or n\$1type near metal\$1oxide near semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:13
S3	402	(level near conversion near circuit) and (semiconductor near integrated near circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:15
S4	10235	interface and (voltage same (low and high)) and MOS and integrated	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:16
S5	9505	S4 and control\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:16
S6	4989	S5 and buffer\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:18
S7	151	S6 and overvoltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:18
S8	402	(level near conversion near circuit) and (semiconductor near integrated near circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:18

S9	1093	326/80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:19
S10	1564	326/81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:19
S11	290	315/160	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:19
S12	26838	semiconductor and (IC or (integrated adj circuit)) and inverter and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:20
S13	373	S12 and ("315"/\$.ccls. or "326"/\$. ccls)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:20